MOSFETs Silicon N-Channel MOS (DTMOSIV)

# TK20V60W

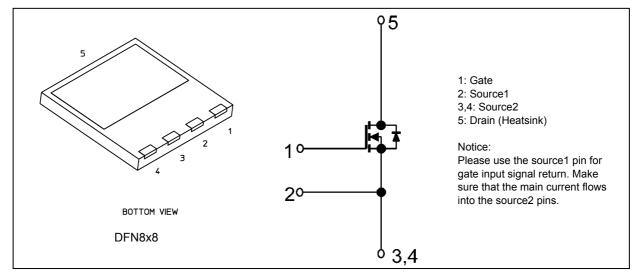
### 1. Applications

Switching Voltage Regulators

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 0.136 \Omega$  (typ.) by used to Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode:  $V_{\rm th}$  = 2.7 to 3.7 V (V\_{\rm DS} = 10 V,  $I_{\rm D}$  = 1 mA)

### 3. Packaging and Internal Circuit



## 4. Absolute Maximum Ratings (Note) ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	600	V
Gate-source voltage		V <sub>GSS</sub>	±30	
Drain current (DC)	(Note 1)	I <sub>D</sub>	20	A
Drain current (pulsed)	(Note 1)	I <sub>DP</sub>	80	
Power dissipation (T <sub>c</sub> = 25°C	:)	PD	156	W
Single-pulse avalanche energy	(Note 2)	E <sub>AS</sub>	200	mJ
Avalanche current		I <sub>AR</sub>	5	Α
Reverse drain current (DC)	(Note 1)	I <sub>DR</sub>	20	
Reverse drain current (pulsed)	(Note 1)	I <sub>DRP</sub>	80	
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature		T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production 2013-03

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R <sub>th(ch-c)</sub>	0.8	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C. Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 14 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 5 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

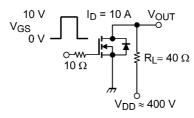
#### 6. Electrical Characteristics

#### 6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±30 V, $V_{DS}$ = 0 V	_	_	±1	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V	_	—	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	600	—	—	V
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	2.7	—	3.7	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A		0.136	0.17	Ω

### 6.2. Dynamic Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 300 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	1680	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	]		7	_	
Output capacitance	C <sub>oss</sub>	1		40	_	
Effective output capacitance	C <sub>o(er)</sub>	$V_{DS}$ = 0 to 400 V, $V_{GS}$ = 0 V		70	_	
Gate resistance	r <sub>g</sub>	V <sub>DS</sub> = OPEN, f = 1 MHz		1.5	_	Ω
Switching time (rise time)	tr	See Figure 6.2.1		25		ns
Switching time (turn-on time)	t <sub>on</sub>	]		50	_	
Switching time (fall time)	t <sub>f</sub>	]		6	_	
Switching time (turn-off time)	t <sub>off</sub>	1	_	100	_	
MOSFET dv/dt ruggedness	dv/dt	V <sub>DD</sub> = 0 to 400 V, I <sub>D</sub> = 5 A	50	_	_	V/ns



Duty  $\leq$  1 %, t<sub>w</sub> = 10  $\mu$ s

#### Fig. 6.2.1 Switching Time Test Circuit

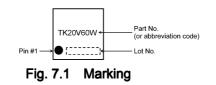
#### 6.3. Gate Charge Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V},  V_{GS} \text{ = } 10  \text{V},  \text{I}_{D} \text{ = } 20  \text{A}$	_	48	—	nC
Gate-source charge 1	Q <sub>gs1</sub>	]	_	11	_	
Gate-drain charge	Q <sub>gd</sub>		_	22	_	

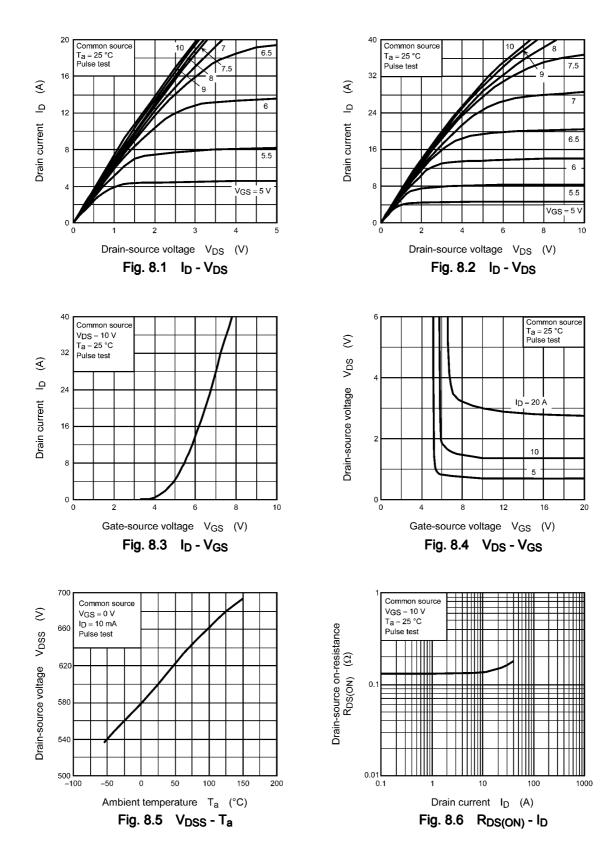
## 6.4. Source-Drain Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

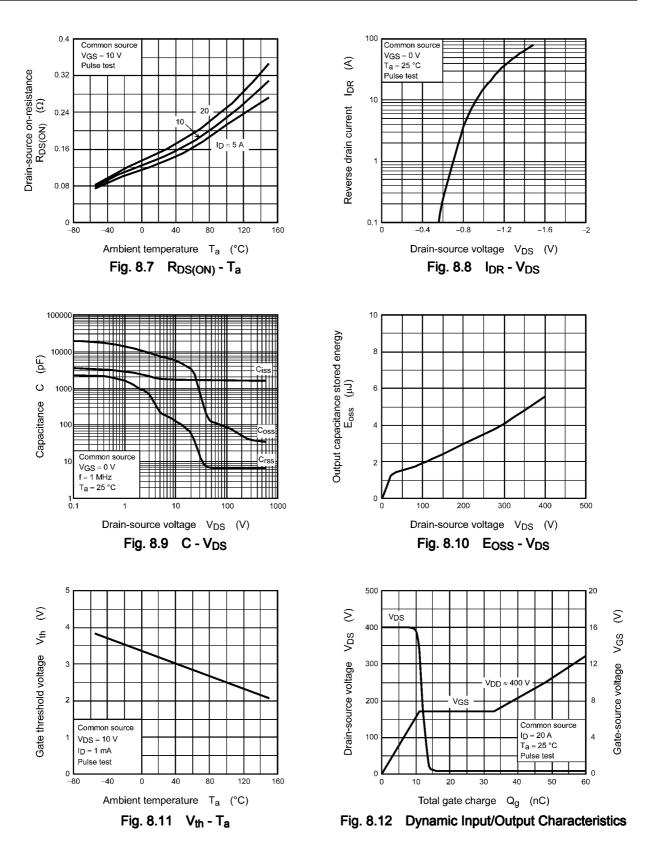
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 20 A, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 10 A, V <sub>GS</sub> = 0 V	_	330	_	ns
Reverse recovery charge	Q <sub>rr</sub>	-dI <sub>DR</sub> /dt = 50 A/μs	_	2.9	_	μC
Peak reverse recovery current	I <sub>rr</sub>		_	16	_	А
Diode dv/dt ruggedness	dv/dt	I <sub>DR</sub> = 10 A, V <sub>GS</sub> = 0 V, V <sub>DD</sub> = 400 V	15			V/ns

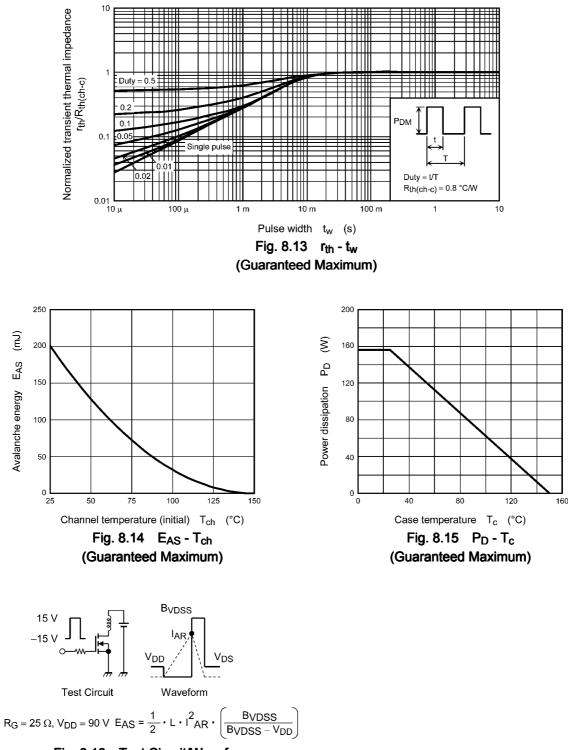
## 7. Marking



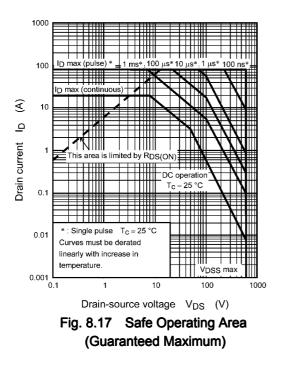
### 8. Characteristics Curves (Note)











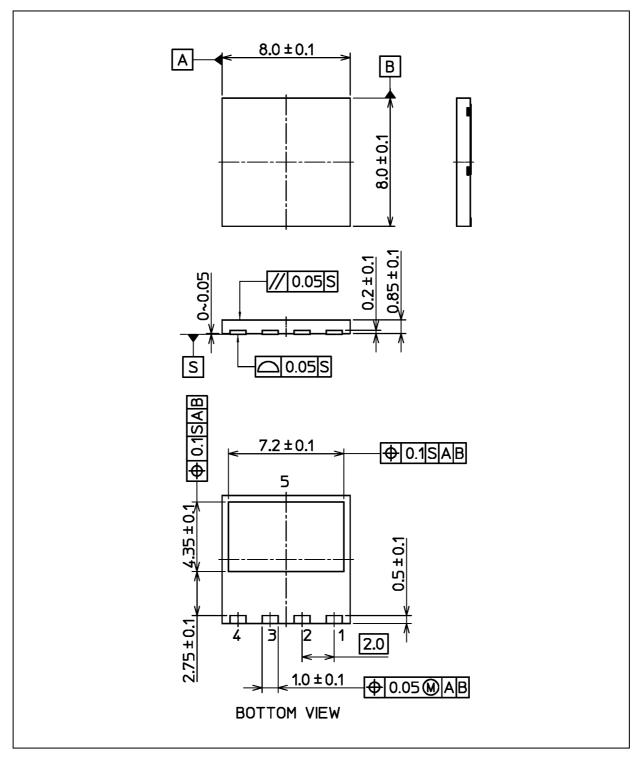
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### Package Dimensions

TK20V60W

Unit: mm



Weight: 0.175 g (typ.)

	Package Name(s)
TOSHIBA: 2-8T1A	
Nickname: DFN8x8	

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